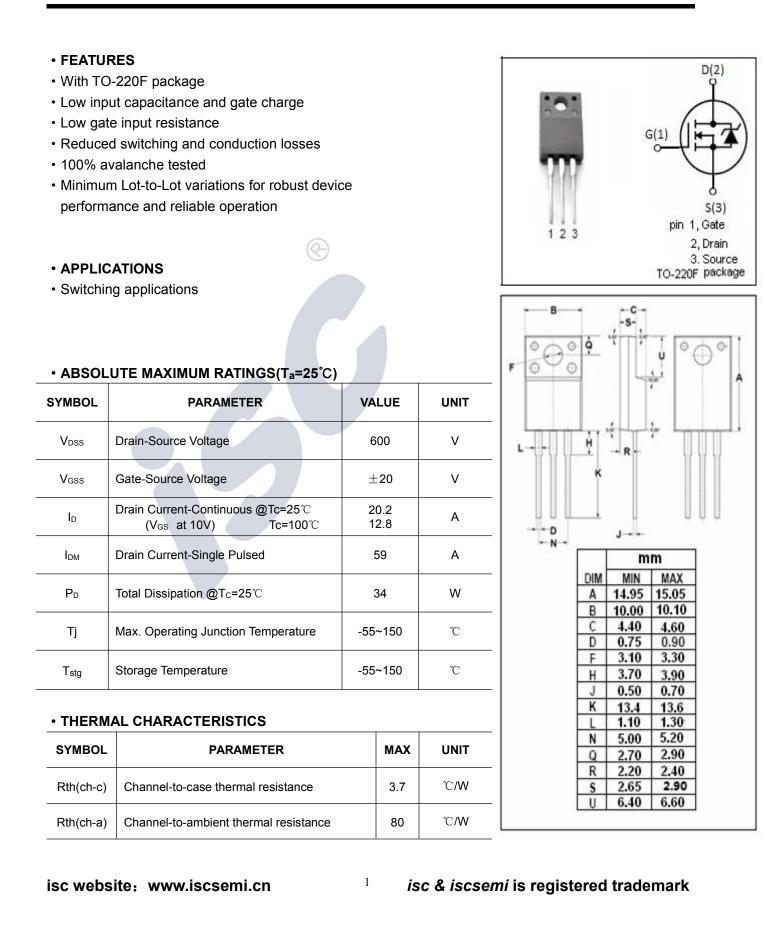


INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

IPA60R190E6





Isc N-Channel MOSFET Transistor

IPA60R190E6

ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	600			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.63mA	2.5	3	3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =9.5A;Tj=25℃ V _{GS} = 10V; I _D =9.5A; Tj=150℃		0.17 0.44	0.19	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V;Tj=25℃ V _{DS} = 600V; V _{GS} = 0V; Tj=150℃		10	1	μA
V _{SDF}	Diode forward voltage	I _{SD} =9.5A, V _{GS} = 0 V		0.9		V



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